

ABSTRACT

A semiconductor device includes a substrate, active regions extending in a first horizontal direction on the substrate, and including first and second active regions spaced apart from each other in a second horizontal direction perpendicular to the first horizontal direction, and third and fourth active regions spaced apart from each other in the second horizontal direction, first to fourth source/drain regions on the first to fourth active regions, first to fourth contact plugs connected to the first to fourth source/drain regions, a first isolation insulating pattern disposed between the first and second contact plugs, and a second isolation insulating pattern disposed between the third and fourth contact plugs, wherein a first length of the first isolation insulating pattern is smaller than a second length of the second isolation insulating pattern in a vertical direction.

FIG. 2C